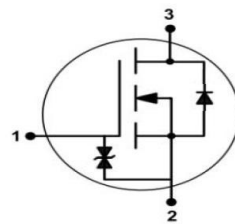
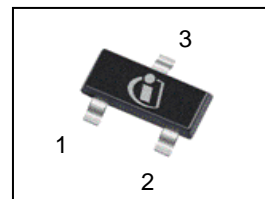


**OptiMOS™ 2 Small-Signal-Transistor**
**Features**

- N-channel
- Enhancement mode
- Ultra Logic level (1.8V rated)
- ESD protected
- Avalanche rated
- Qualified according to AEC Q101
- 100% lead-free; RoHS compliant
- Halogen-free according to IEC61249-2-21

**Product Summary**

$V_{DS}$	20	V
$R_{DS(on),max}$	$V_{GS}=2.5\text{ V}$	57
	$V_{GS}=1.8\text{ V}$	82
$I_D$	2.3	A


**PG-SOT23**


Type	Package	Tape and Reel	Marking	Halogen Free	Packing
BSS806NE	SOT23	H6327: 3000 pcs/ reel	YIs	Yes	Non dry

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_A=25\text{ °C}$	2.3	A
		$T_A=70\text{ °C}$	1.9	
Pulsed drain current	$I_{D,pulse}$	$T_A=25\text{ °C}$	9.3	
Avalanche energy, single pulse	$E_{AS}$	$I_D=2.3\text{ A}$ , $R_{GS}=25\ \Omega$	10.8	mJ
Reverse diode $dv/dt$	$dv/dt$	$I_D=2.3\text{ A}$ , $V_{DS}=16\text{ V}$ , $di/dt=200\text{ A}/\mu\text{s}$ , $T_{j,max}=150\text{ °C}$	6	kV/ $\mu\text{s}$
Gate source voltage	$V_{GS}$		$\pm 8$	V
Power dissipation <sup>1)</sup>	$P_{tot}$	$T_A=25\text{ °C}$	0.5	W
Operating and storage temperature	$T_j$ , $T_{stg}$		-55 ... 150	°C
ESD Class		JESD22-A114 -HBM	1C(1kV to 2kV)	
Soldering Temperature			260 °C	
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - ambient	$R_{thJA}$	minimal footprint <sup>1)</sup>	-	-	250	K/W
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**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	20	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=11\text{ }\mu\text{A}$	0.3	0.55	0.75	
Drain-source leakage current	$I_{DSS}$	$V_{DS}=20\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	-	1	$\mu\text{A}$
		$V_{DS}=20\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ °C}$	-	-	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=8\text{ V}, V_{DS}=0\text{ V}$	-	-	6	$\mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=1.8\text{ V}, I_D=1.3\text{ A}$	-	57	82	$\text{m}\Omega$
		$V_{GS}=2.5\text{ V}, I_D=2.3\text{ A}$	-	41	57	
Transconductance	$g_{fs}$	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=1.9\text{ A}$		9	-	S

<sup>1)</sup> Performed on 40mm<sup>2</sup> FR4 PCB. The traces are 1mm wide, 70 $\mu\text{m}$  thick and 20mm long; they are present on both sides of the PCB.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=10\text{ V},$ $f=1\text{ MHz}$	-	370	529	pF
Output capacitance	$C_{oss}$		-	118	169	
Reverse transfer capacitance	$C_{rss}$		-	20	29	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=10\text{ V}, V_{GS}=2.5\text{ V},$ $I_D=2.3\text{ A}, R_{G,ext}=6\ \Omega$	-	7.5	-	ns
Rise time	$t_r$		-	9.9	-	
Turn-off delay time	$t_{d(off)}$		-	12.0	-	
Fall time	$t_f$		-	3.7	-	

**Gate Charge Characteristics**

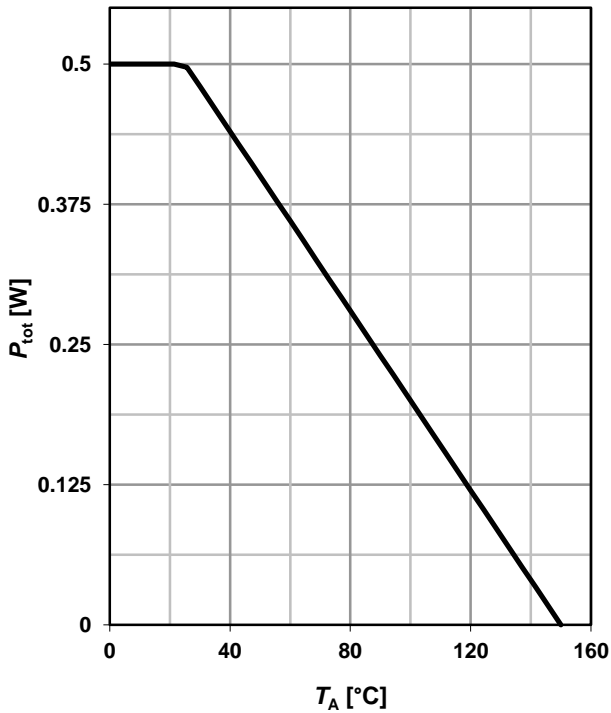
Gate to source charge	$Q_{gs}$	$V_{DD}=10\text{ V}, I_D=2.3\text{ A},$ $V_{GS}=0\text{ to }2.5\text{ V}$	-	0.55	-	nC
Gate to drain charge	$Q_{gd}$		-	0.58	-	
Gate charge total	$Q_g$		-	1.7	-	
Gate plateau voltage	$V_{plateau}$		-	1.5	-	V

**Reverse Diode**

Diode continuous forward current	$I_S$	$T_A=25\text{ }^\circ\text{C}$	-	-	0.5	A
Diode pulse current	$I_{S,pulse}$		-	-	9.3	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=2.3\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0.82	1.1	V
Reverse recovery time	$t_{rr}$	$V_R=10\text{ V}, I_F=2.3\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	11	-	ns
Reverse recovery charge	$Q_{rr}$		-	3.3	-	nC

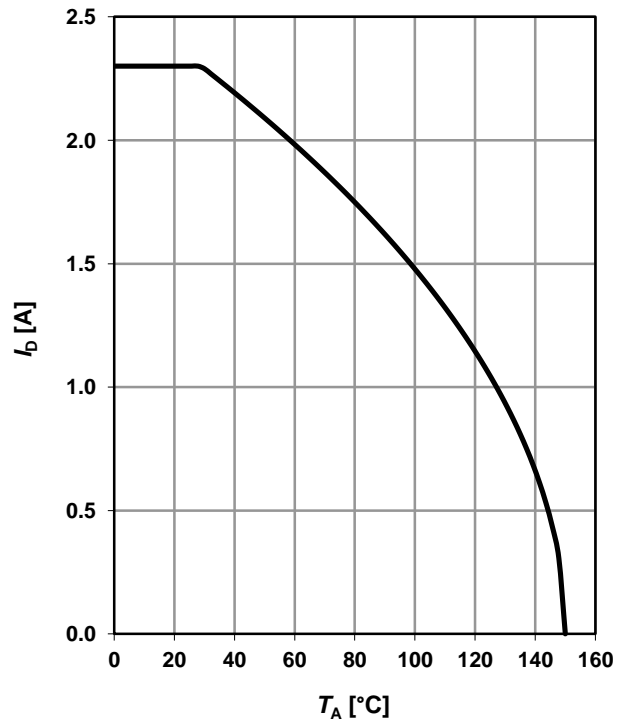
**1 Power dissipation**

$P_{tot}=f(T_A)$



**2 Drain current**

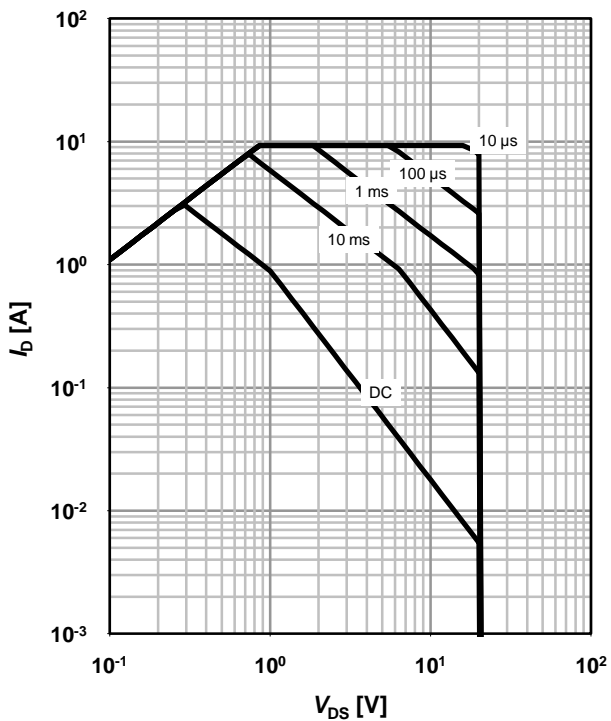
$I_D=f(T_A); V_{GS} \geq 2.5 V$



**3 Safe operating area**

$I_D=f(V_{DS}); T_A=25\text{ °C}; D=0$

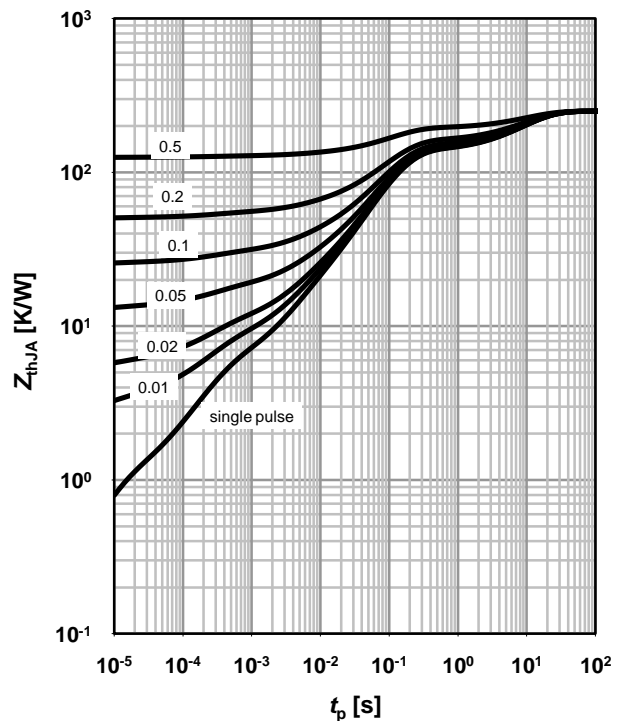
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJA}=f(t_p)$

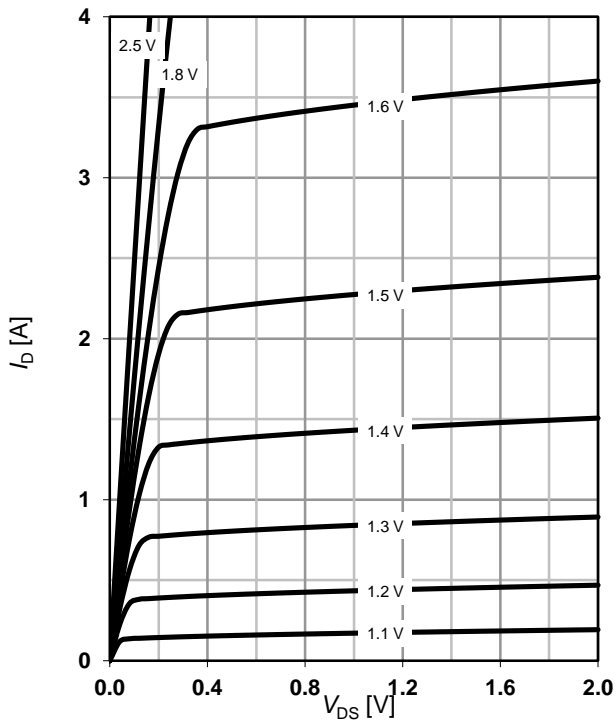
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

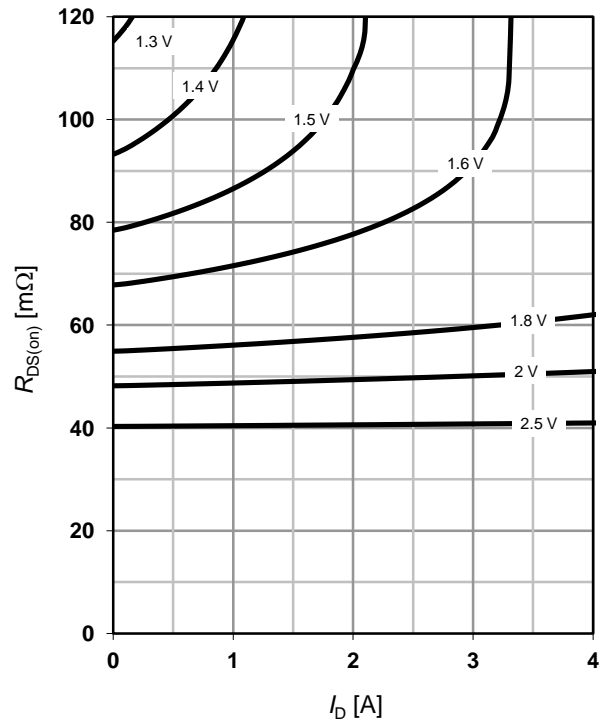
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

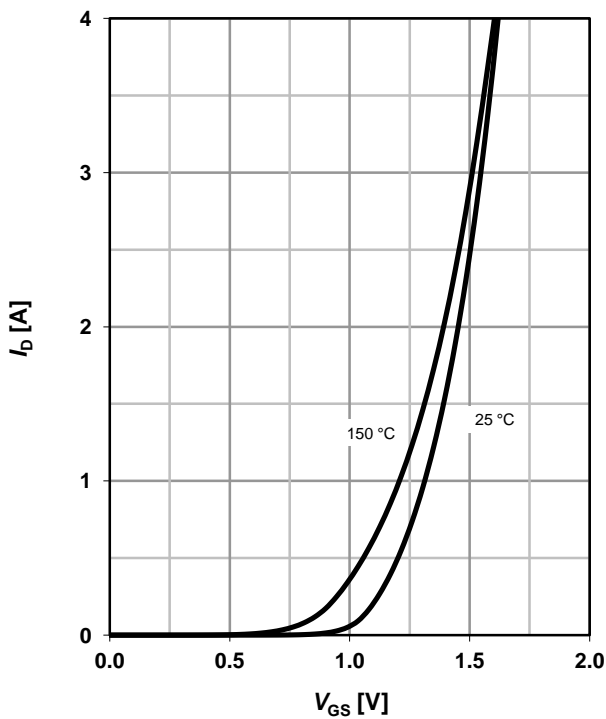
$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

parameter:  $V_{GS}$



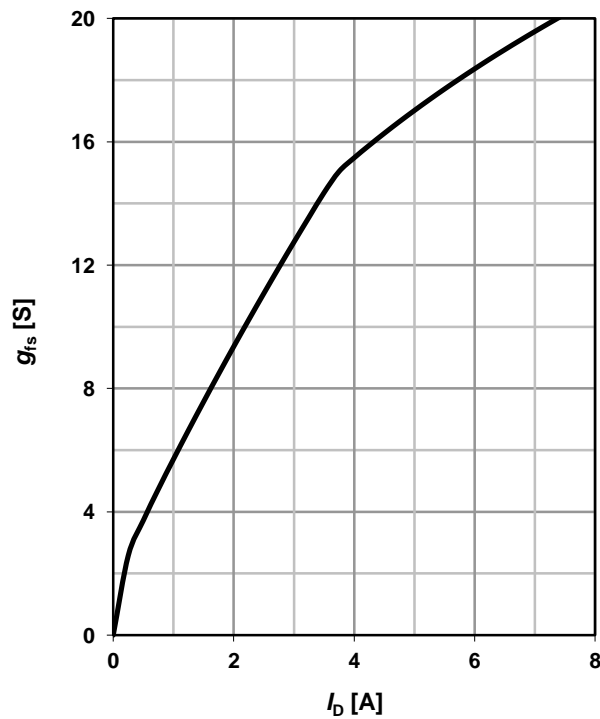
**7 Typ. transfer characteristics**

$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$



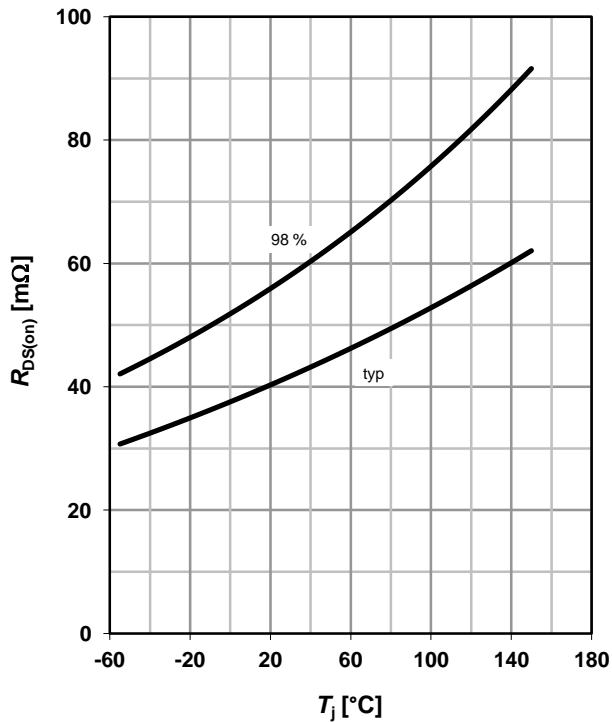
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ °C}$



**9 Drain-source on-state resistance**

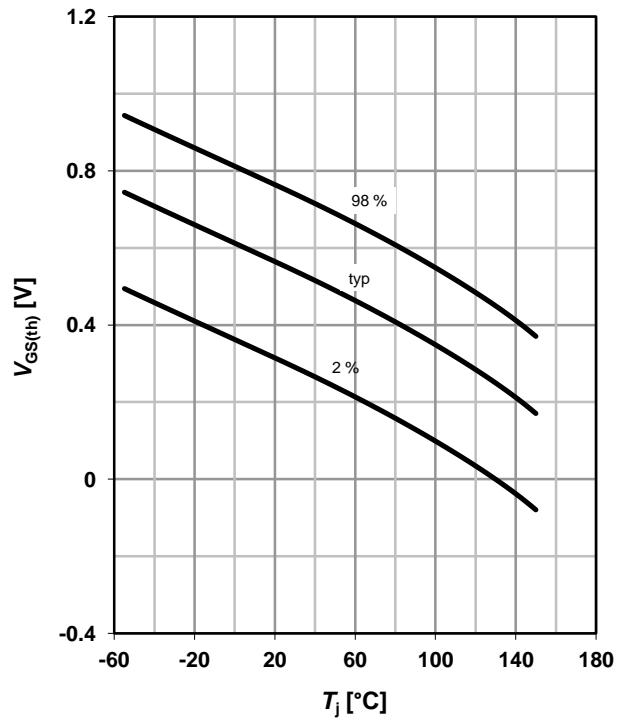
$R_{DS(on)}=f(T_j); I_D=2.3\text{ A}; V_{GS}=2.5\text{ V}$



**10 Typ. gate threshold voltage**

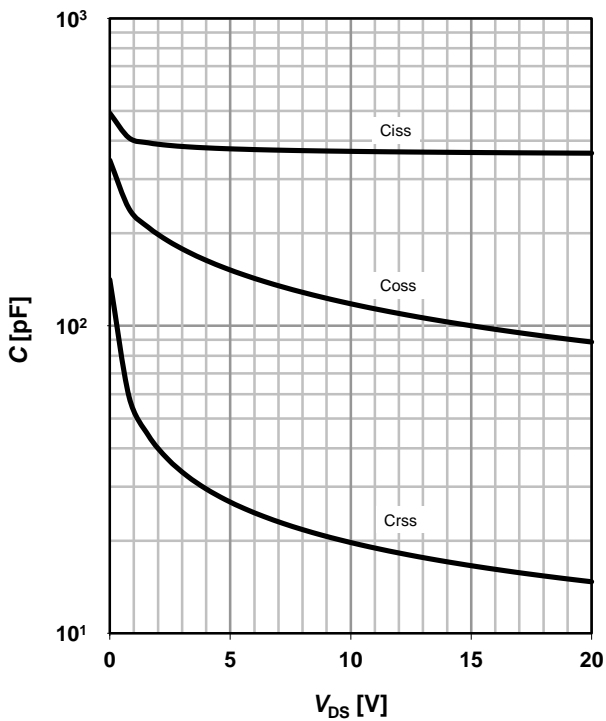
$V_{GS(th)}=f(T_j); V_{DS}=V_{GS}; I_D=11\ \mu\text{A}$

parameter:  $I_D$



**11 Typ. capacitances**

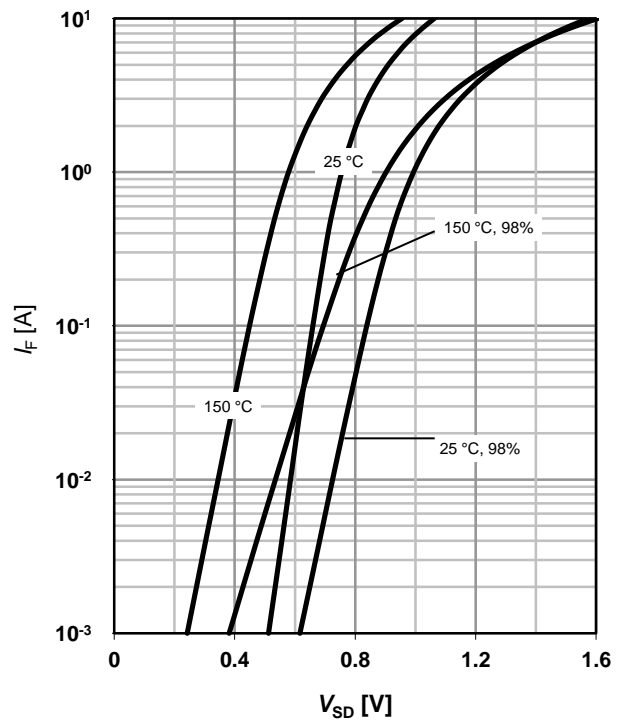
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}; T_j=25^\circ\text{C}$



**12 Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

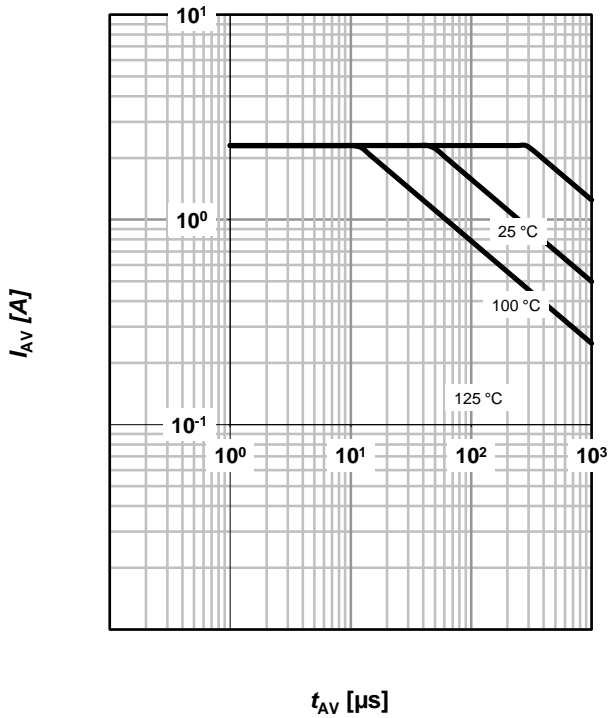
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

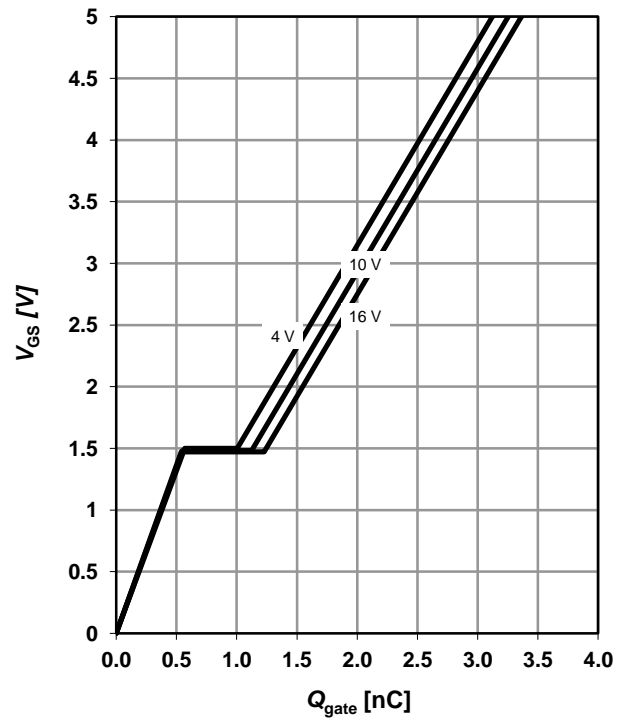
parameter:  $T_{j(\text{start})}$



**14 Typ. gate charge**

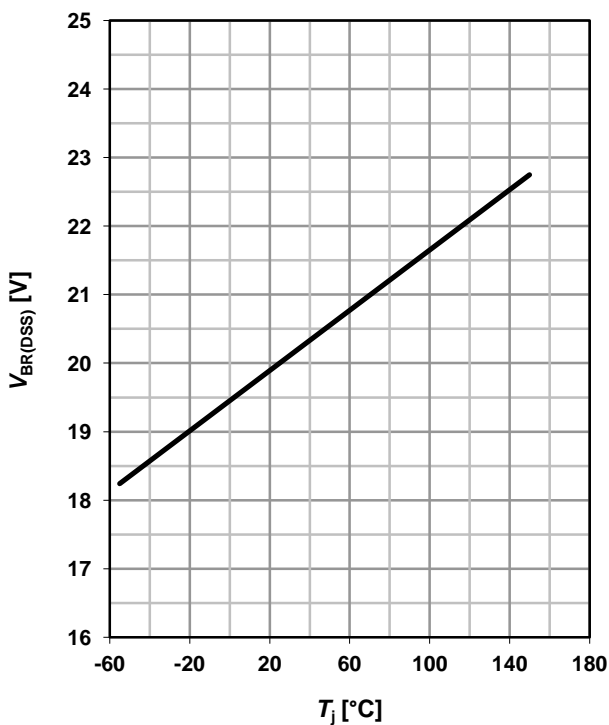
$V_{GS}=f(Q_{\text{gate}}); I_D=2.3 \text{ A pulsed}$

parameter:  $V_{DD}$

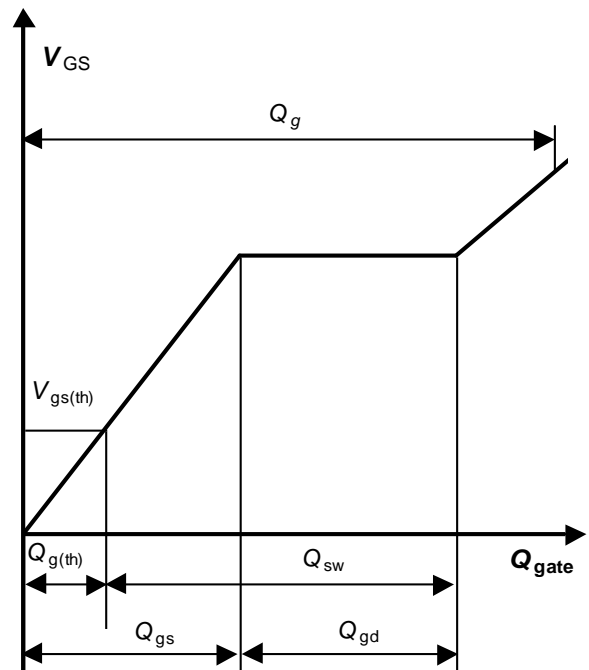


**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=250 \mu\text{A}$

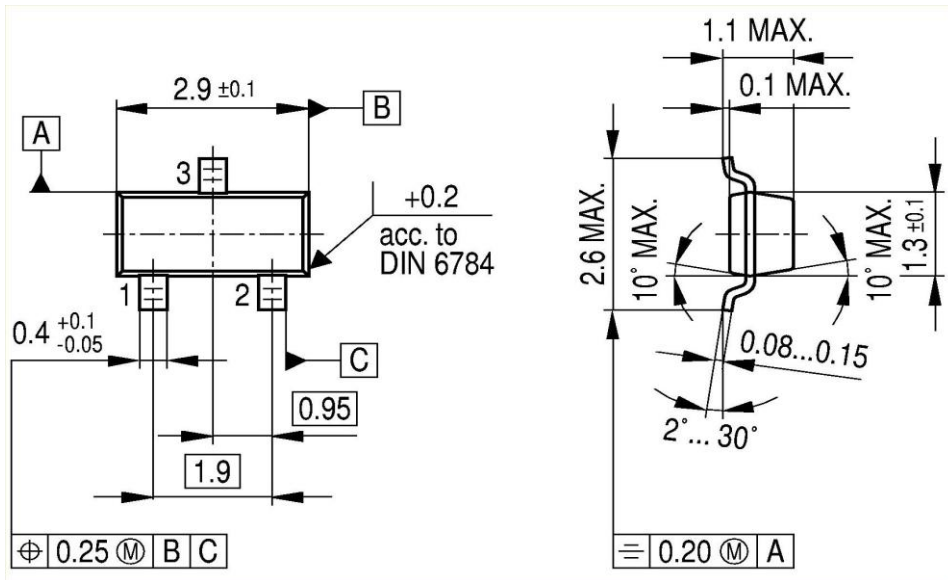


**16 Gate charge waveforms**

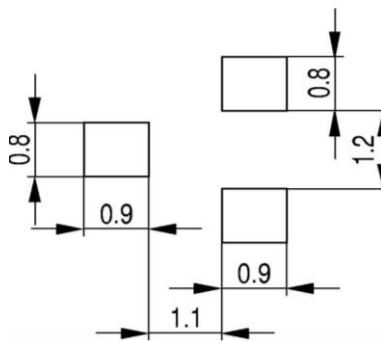


SOT23

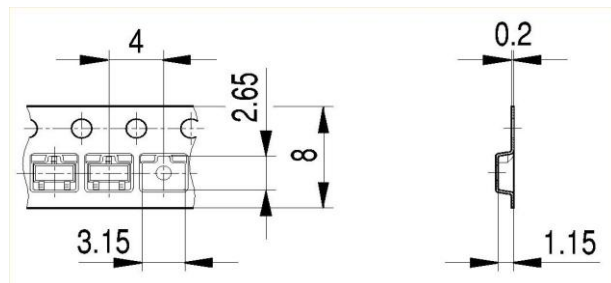
Package Outline:



Footprint:



Packaging:



Dimensions in mm



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